

Tailoring Valley Polarization of Interlayer Excitons in van der Waals Heterostructure toward Optical Communication

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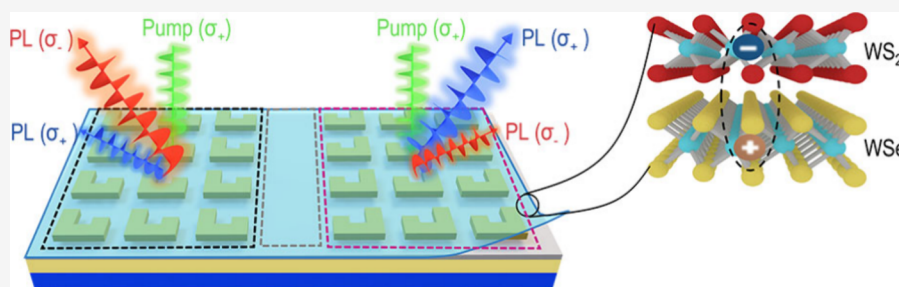
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ABSTRACT: Controlling the valley polarization of interlayer excitons in van der Waals heterostructures is essential for developing valleytronic devices. Here, we demonstrate the manipulation of valley polarization of interlayer excitons in a monolayer WSe_2/WS_2 heterostructure using a dual-handedness metasurface. This metasurface, composed of left- and right-handed gold nanoantenna arrays, exhibits distinct chiral optical responses. Introducing the metasurface into heterostructures significantly enhances the degree of interlayer exciton valley polarization, which quantitatively corresponds to the circular dichroism (CD) of interlayer excitons, via chiral Purcell effects. A negative CD of -16% is yielded via the left-handed metasurface, and a positive CD of $+25\%$ is harvested via the right-handed metasurface under σ_+ excitation of 532 nm at 77 K . Moreover, the CD is tunable with excitation wavelength, reaching a maximum of 38% at 620 nm under σ_- excitation, the highest value from interlayer excitons reported so far without applying external fields. Further, we demonstrate that this platform enables direct and byte-invert arithmetic operations for information transmission. This capability highlights its potential for error detection in valleytronics-based optical communication systems.

KEYWORDS: Transition metal dichalcogenides, heterostructures, interlayer excitons, chiral metasurfaces, valley polarization enhancement

Two-dimensional transition-metal dichalcogenides (TMDs) are promising candidates for valleytronic applications, such as valley-addressable laser,¹ nanophotonic circuit,² and valley transistor.^{3,4} The broken inversion symmetry and strong spin–orbital interaction in monolayer TMDs lead to two degenerate yet inequivalent valley states, K and K', in their band structures, offering a new degree of freedom to store and process information.^{5–7} The electrons in these two valley states can be selectively excited with circularly polarized light, generating an imbalanced carrier population in K or K' valleys. Therefore, the circularly polarized photoluminescence (PL) manifests unequal intensity for two chiral components.^{8–10} Circular dichroism (CD)^{5,11–13} can be defined as $\text{CD} = (I_{\text{co}} - I_{\text{cross}})/(I_{\text{co}} + I_{\text{cross}})$, where I_{co} is the intensity of the copolarized light and I_{cross} is the intensity of the cross-polarized light. Previous studies have shown valley-polarized PL from intralayer exciton in monolayer molybdenum disulfide (MoS_2),^{5,8,9,14} molybdenum diselenide (MoSe_2),^{15,16} tungsten disulfide (WS_2),^{17,18} and tungsten diselenide (WSe_2).^{10,19,20} However, electron–hole exchange interactions lead to rapid valley depolarization of intralayer

excitons in monolayer TMDs within picoseconds, which restricts their applications in valleytronic devices.^{21–24}

Alternatively, stacking different TMD monolayers to a van der Waals (vdW) heterostructure gives rise to interlayer excitons, where the electron and hole are spatially separated in different layers.^{25–27} Unlike intralayer excitons, interlayer excitons exhibit a longer valley lifetime (nanoseconds) due to the small overlap of electron–hole wave functions.^{28–31} To date, manipulation of CD in TMDs often requires an externally applied electric field,^{10,32,33} magnetic field,^{34–38} electrochemical doping,³⁹ and precise twist-angle engineering,^{12,40–42} which are challenging for the broad applications of valleytronic devices. On the other hand, metasurfaces have become a key tool in enhancing the optical properties of two-dimensional

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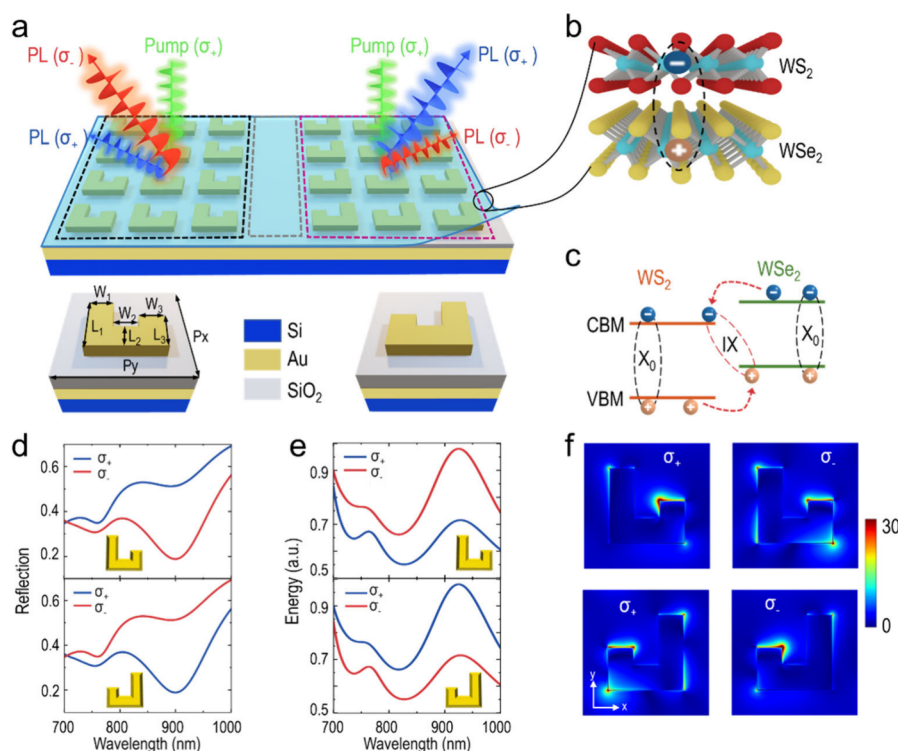


Figure 1. (a) Schematic of the monolayer WSe₂/WS₂ heterostructure-metasurface structure, where the WSe₂/WS₂ heterostructure is placed on the L-MS (black-dashed frame), R-MS (red-dashed frame), and the separating blank region of the metasurface (gray dashed frame), respectively. The unit cells of L-MS (left) and R-MS (right) are shown in the lower row, with the geometrical parameters $L_1 = 300$ nm, $L_2 = 100$ nm, $L_3 = 170$ nm, $W_1 = W_2 = W_3 = 100$ nm, and $P_x = P_y = 500$ nm, and the height of the Au nanoantenna is 30 nm. (b) Schematic side view of the WSe₂/WS₂ heterostructure. The dashed ellipse depicts the interlayer exciton with holes and electrons in WSe₂ and WS₂, respectively. (c) Type-II band alignment in monolayer WSe₂/WS₂ heterostructure facilitated the formation of interlayer excitons. (d) The simulated reflection spectra of the L-MS and R-MS. (e) The calculated total electromagnetic energy (U) of the L-MS and R-MS obtained by integrating the electromagnetic energy in a single unit cell from the nanoantenna top surface down to the gold substrate. (f) The simulated electric field mapping across the unit cell for the L-MS and R-MS with the excitation of σ_+ and σ_- incidence at a resonant wavelength of 905 nm.

materials.^{43,44} Recently, chiral metasurfaces with broken mirror symmetry^{45,46} have attracted much attention for their pronounced optical activity and CD.^{47–50} Leveraging the advantages of chiral metasurfaces, the approach can be applied to tune the valley polarization of intralayer excitons in monolayer TMDs of MoS₂,^{51–54} WS₂,⁵⁵ and WSe₂.^{11,43,56–58} This strategy controls the interaction between the plasmonic resonances of the chiral metasurface and the valley-polarized intralayer exciton to enhance the emission rates in a specific valley. Naturally, combining chiral metasurfaces with van der Waals heterostructures may offer a promising way to modulate the valley polarization of interlayer excitons, which benefit from both the chiral optical responses of metasurfaces and the long lifetime of the interlayer exciton in heterostructures.

In this Letter, we report a dual-handedness metasurface designed to enhance the CD of interlayer excitons in a WSe₂/WS₂ heterostructure and show its potential optical communication applications. Our metasurface comprises left- and right-handed sections, separated by a blank region. The CD of interlayer excitons in the blank region is 4% at 77 K. It reaches -16% via the left-handed metasurface and $+25\%$ via the right-handed metasurface under an σ_+ excitation of 532 nm at the same temperature. Helicity-resolved photoluminescence excitation (PLE) spectroscopy reveals an increased CD up to 38% as the wavelength of σ_- excitation corresponds to the bandgap of WS₂. Here σ_+ denotes right-handed circular polarization and σ_- denotes left-handed circular polarization.

Furthermore, we demonstrate the heterostructure-metasurface system as a potential bifunctional device for optical information transmission. We encode the input message “NJU” with Morse code. When the encoded light is focused on the right-handed metasurface, the output message remains “NJU”. However, focusing on the left-handed metasurface results in the output message “REED”. This experiment confirms the capability of this device for both direct and byte-inverted transmission, which is beneficial for error detection in optical communication.

DESIGNING A DUAL-HANDEDNESS METASURFACE TO UPHOLD WSe₂/WS₂ HETEROSTRUCTURE

A schematic of the designed structure is illustrated in Figure 1a. The dual-handedness metasurface is fabricated on a SiO₂-gold bilayer on a silicon substrate. In the x – y plane, the metasurface is divided into three regions: the left part of the metasurface (L-MS) is a η -shaped gold nanoantenna array; the right part of the metasurface (R-MS) contains a mirror-imaged array of the L-MS nanoantenna; and the center part does not have any structure and serves as a separating blank region. To investigate the chiral optical response of the device, we perform finite-difference time-domain (FDTD) simulations. The resonant wavelength is designed at 905 nm (the interlayer exciton PL wavelength) by selecting $L_1 = 300$ nm, $L_2 = 100$ nm, $L_3 = 170$ nm, and $W_1 = W_2 = W_3 = 100$ nm, with a spatial

lattice period of 500 nm. The calculated reflection spectra of L-MS and R-MS are shown in Figure 1d. It shows that the resonance of the L-MS and R-MS both occur around 905 nm. We simulate the electric and magnetic fields distribution in the gold nanoantenna-SiO₂-gold cavity and calculate the total electromagnetic energy U as the sum of the electric and magnetic energy,⁵⁹ $U = \frac{1}{4} \int \left(\frac{d(\omega\epsilon)}{d\omega} |E|^2 + \frac{d(\omega\mu)}{d\omega} |H|^2 \right) d^3r$ where E and H are the electric and magnetic fields, and ϵ and μ are the permittivity and permeability, respectively. The integration is carried out across a single unit cell, from the top surface of the nanoantenna to the gold substrate, where the dispersive materials are considered. On the L-MS, a high resonance peak in the total electromagnetic energy is observed in σ_- excitation, indicating a localized plasmonic resonance mode with strong electromagnetic confinement. This resonance leads to significantly higher energy under σ_- excitation than σ_+ excitation (see the upper panel of Figure 1e). In contrast, on the R-MS, the total energy is more significant in σ_+ excitation (as shown in the lower panel of Figure 1e). This difference is attributed to the localized plasmonic mode, which confines more electromagnetic energy for σ_+ excitation. To further investigate the physical mechanism of this energy difference, we simulate the electric field distribution on the surface of the gold nanoantenna at the resonant wavelength (905 nm) in both σ_+ and σ_- excitations. It follows that on the L-MS, the electric field intensity is more vigorous for σ_- excitation (upper panel of Figure 1f). In contrast, on the R-MS, the electric field is more substantial for σ_+ excitation (lower panel of Figure 1f). The enhanced electric field intensity indicates a higher concentration of electromagnetic energy within the cavity, leading to a higher total electromagnetic energy U . These results confirm that the η -shaped or its mirror-imaged gold nanoantenna exhibits strong optical chirality^{60,61} at the resonant wavelength due to the broken inversion symmetry, resulting in distinct optical responses to σ_+ and σ_- incidence. Structural asymmetry is crucial in generating different near-field enhancements, leading to distinct chiral optical response.

CHIRAL PURCELL EFFECTS ENHANCE THE DEGREE OF THE INTERLAYER EXCITON VALLEY POLARIZATION

In each unit cell, the sandwich structure realizes the optical field constraint by vertically reflecting the upper gold nanoantenna and the lower solid gold layer. Moreover, in the horizontal direction, it relies on the localized surface plasmon resonance effect of the top gold nanoantenna to achieve optical field localization. Eventually, it forms a nanocavity system that limits the optical field in three-dimensional space.

To modulate the degree of interlayer exciton valley polarization, which quantitatively corresponds to the CD of interlayer excitons,¹³ the monolayer WSe₂/WS₂ heterostructure is placed on the dual-handedness metasurface, as illustrated in Figure 1a,b. The heterostructure exhibits type-II band alignment: the electrons of WSe₂ hop to the conduction band of WS₂, and the holes of WS₂ hop to the valence band of WSe₂. Meanwhile, the interlayer exciton is naturally produced by the spatially separated electron–hole pairs due to Coulomb interactions, as shown in Figure 1c. Considering that each unit cell of the gold metasurface acts as a chiral nanocavity, the helicity-dependent strong electric fields may induce the chiral

Purcell effect⁵⁴ in the WSe₂/WS₂ heterostructure-metasurface structure.

Now we consider that the valley-polarized emission can be modified by the chiral Purcell effect^{54,56,62} in the current WSe₂/WS₂ heterostructure-metasurface structure. We first define ρ^+ (or ρ^-) as the local density of states (LDOS) on the metasurface with σ_+ (or σ_-) dipole excitation and ρ_0 as the LDOS in the vacuum. We calculate the normalized circularly polarized LDOS,^{54,63} i.e., ρ^+/ρ_0 (or ρ^-/ρ_0). Figure 2a shows

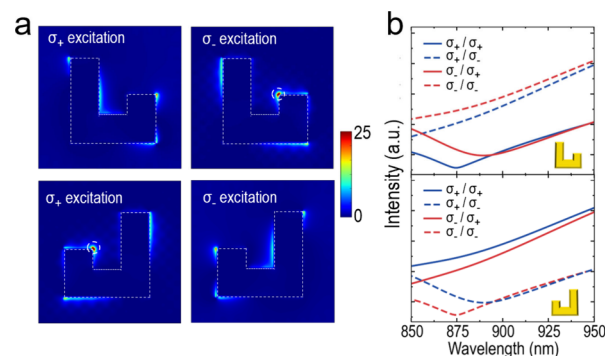


Figure 2. (a) LDOS of L-MS and R-MS with σ_+ and σ_- dipole excitation at the resonant wavelength of 905 nm, respectively. (b) The simulated circularly polarized far-field PL spectra out of L-MS and R-MS, respectively. The circularly polarized far field PL is calculated by placing the circularly polarized dipoles at the LDOS maximum spot (marked by the white dashed circle in Figure 2a). Here, $\sigma_+/ \sigma_\pm$ stands for the $\sigma_\pm$ resolved far field PL spectra excited by σ_+ dipoles, and $\sigma_-/ \sigma_\pm$ stands for the $\sigma_\pm$ resolved far field PL spectra excited by σ_- dipoles.

the simulated LDOS of L-MS and R-MS with both σ_+ and σ_- dipole excitations at a resonant wavelength of 905 nm. It is shown that for L-MS, the LDOS ρ^-/ρ_0 reaches the maximum at the corner marked by the white dashed circle under σ_- dipoles excitation (to see the upper right panel of Figure 2a). This suggests⁶³ that the L-MS promotes a higher spontaneous emission rate for σ_- dipoles, leading to a higher Purcell factor for σ_- dipoles. Further if placing the circularly polarized dipoles at the ρ^-/ρ_0 maximum spot on L-MS, the calculated far-field PL spectra out of the L-MS (as shown in the upper panel of Figure 2b) reveal that the emission modified by LDOS always favors stronger σ_- light regardless of the incident polarization. Similarly, for R-MS, the LDOS ρ^+/ρ_0 reaches the maximum at the corner marked by the dashed circle under σ_+ dipole excitation (to see the lower left panel of Figure 2a), and the emission out of the R-MS always generates stronger σ_+ light (as shown in the lower panel of Figure 2b). All these simulations indicate that the valley-polarized emission in this system is significantly modified by the chiral Purcell effects in L-MS and R-MS. More simulations are given in Figure S1 of Supporting Information.

SAMPLE FABRICATION AND VALLEY POLARIZATION OF INTERLAYER EXCITONS

Experimentally, we first fabricate the sample by depositing a 100 nm-thick gold reflecting layer and a 90 nm-thick SiO₂ dielectric layer on a Si substrate by magnetron sputtering. Then, we fabricated the gold unit cell arrays using e-beam lithography to make the left (L-MS) and right (R-MS) parts of the metasurface. The L-MS and R-MS are separated by 5 μm , where no structures are fabricated. The mechanically exfoliated WSe₂ monolayer is transferred to cover three regions of the

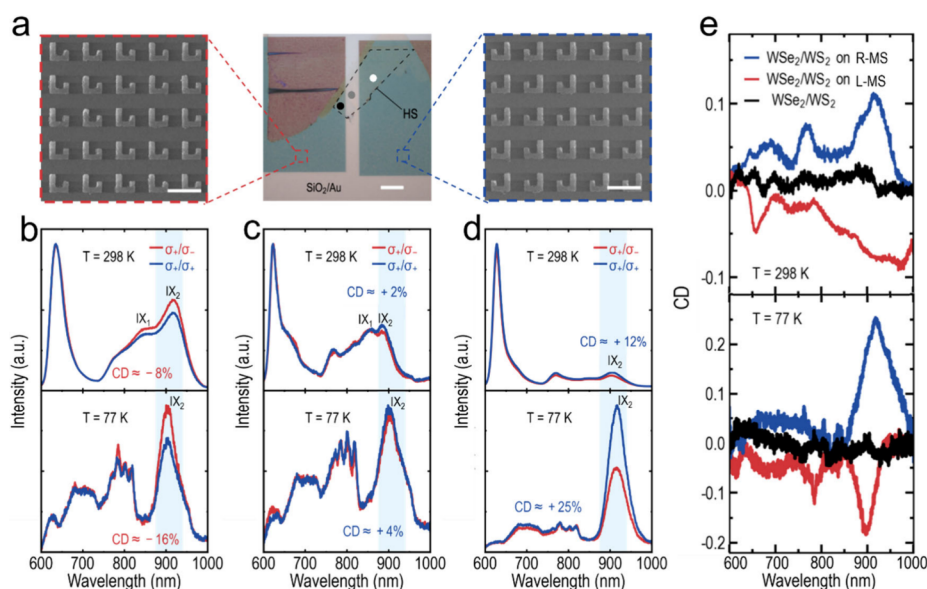


Figure 3. (a) The optical microscope image of the WSe₂/WS₂ heterostructure-metasurface, where heterostructure flake is in the dashed black area. Here the scale bar is 10 μ m. Left and right show the scanning electron micrographs of metasurfaces, where each scale bar is 500 nm. The measured valley-polarized PL spectra of WSe₂/WS₂ heterostructure at both 298 K and 77 K, which covers on: (b) the L-MS, (c) the separating blank region of the metasurface, and (d) the R-MS, respectively. Here, IX₁ and IX₂ are marked, and σ_+ / σ_- stands for the $\sigma_{\pm}$ resolved PL spectra excited by σ_+ incidence in (b)–(d). (e) The circular dichroism spectra of the bare WSe₂/WS₂ heterostructure (black) and the heterostructure covering the metasurface (red, blue) at 298 K and 77 K, respectively.

metasurface using the dry transfer method. A mechanically exfoliated WS₂ monolayer is transferred over the WSe₂ monolayer (about 0° twist) using the same method. According to ref 64, the interlayer exciton PL wavelength in a 0° stacked WS₂/WSe₂ heterostructure is around 905 nm, which aligns with the resonance wavelength of the chiral structures we designed. Figure 3a shows the optical micrograph of the WSe₂/WS₂ heterostructure-metasurface. The black, gray, and white dots represent the excitation sites on the three distinct regions marked by the dashed line frames in Figure 1a, respectively. Scanning electron micrographs of the L-MS and R-MS are shown in Figure 3a as well. Circularly polarized PL can determine the valley polarization of the interlayer exciton in the WSe₂/WS₂ heterostructure. In the experiments, we utilize σ_+ (σ_-) incidence to excite the heterostructure and then analyze both σ_+ and σ_- components of the PL signal. The excitation wavelength is 532 nm, corresponding to an energy ($E_{\text{pump}} = 2.33$ eV) much higher than that of the neutral intralayer excitons in monolayer WS₂ ($E_{X_0} = 2$ eV) and WSe₂ ($E_{X_0} = 1.66$ eV). This configuration ensures the excitation of the interlayer excitons at 905 nm. Figure 3b–d illustrates the valley-polarized PL spectra of the WSe₂/WS₂ heterostructure on the L-MS, the separating blank region, and the R-MS, respectively. Here, σ_+ / $\sigma_{\pm}$ stands for the $\sigma_{\pm}$ resolved PL spectra excited by the σ_+ incidence.

At room temperature, the heterostructure exhibits four PL peaks: neutral intralayer excitons (X_0) in monolayer WS₂ at 620 nm, neutral intralayer excitons (X_0) in monolayer WSe₂ at 765 nm, and two interlayer excitons (IX₁ and IX₂) in the near-infrared region. For the WSe₂/WS₂ heterostructure on the separating blank region of the metasurface, the valley-resolved PL spectra indicate that the CD of IX₂ is about 2% at ambient temperature (upper panel of Figure 3c). Meanwhile, for the WSe₂/WS₂ heterostructure on L-MS, the CD of IX₂ exhibits a sign reverse and reaches $\sim -8\%$ (upper panel of Figure 3b).

Similarly, for the WSe₂/WS₂ heterostructure on R-MS, the CD of IX₂ is increased to about 12% (upper panel of Figure 3d).

When the temperature is dropped to 77 K, the IX₂ exciton dominates. The CD of the IX₂ on the separating blank region of the metasurface is increased to about 4% (lower panel of Figure 3c). More specifically, the CD of IX₂ on L-MS and R-MS enhances from $\sim -8\%$ to $\sim -16\%$ and from $\sim +12\%$ to $\sim +25\%$, respectively (lower panel of Figure 3b,d). Figure 3e compares the CD of WSe₂/WS₂ heterostructure on the L-MS, separating blank region, and R-MS at 298 K (upper panel of Figure 3e) and 77 K (lower panel of Figure 3e), respectively. Therefore, by covering the WSe₂/WS₂ heterostructure on R-MS, the CD of IX₂ is enhanced, while on L-MS, the CD is inverted in sign and the value is enhanced as well. These results confirm that we are able to manipulate the valley polarization of interlayer excitons in the WSe₂/WS₂ heterostructure at 298 and 77 K. The PL spectra excited by σ_- light are shown in Supporting Information Figure S2.

To investigate the effect of excitation wavelength on the CD of IX₂, we utilize helicity-resolved photoluminescence excitation (PLE) spectroscopy to measure the dependence of interlayer exciton PL intensity on the excitation wavelength under σ_+ and σ_- excitation, respectively. The WSe₂/WS₂ heterostructure on the L-MS is excited with σ_- light possessing an excitation wavelength ranging from 510 to 620 nm. The detected σ_- and σ_+ components of the PL signal near the IX₂ wavelength (from 875 to 940 nm) at 77 K are shown in Figure 4a. It can be observed that the PL intensity increases as the excitation wavelength approaches 620 nm (approximately corresponding to the bandgap of WS₂). This enhancement is attributed to the increased absorption near the excitation wavelength and hence the increased exciton formation rate, thus resulting in an amplified PL signal. Actually when the excitation wavelength approaches 620 nm, the photon energy matches the direct bandgap of monolayer WS₂, leading to electronic transitions primarily from the valence band

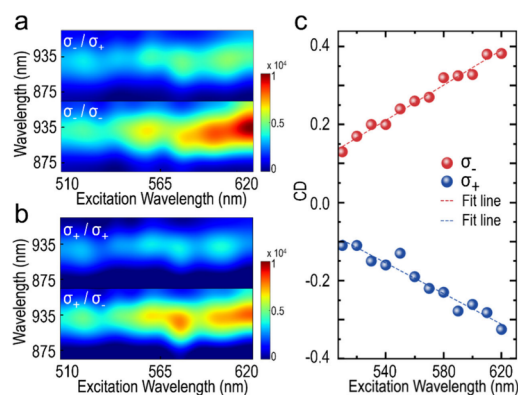


Figure 4. The interlayer exciton PLE spectra at 77 K in the WSe₂/WS₂ heterostructure on the L-MS. The measured valley-polarized interlayer exciton PL spectra plotted as a function of excitation wavelength with (a) σ_- excitation and (b) σ_+ excitation. Here, σ_-/σ_+ stands for the $\sigma_\pm$ resolved PL spectra excited by σ_- incidence, and σ_+/σ_- stands for the $\sigma_\pm$ resolved PL spectra excited by σ_+ incidence. (c) The CD value measured at 910 nm as the excitation wavelength was varied from 510 to 620 nm. The blue and red dots represent the CD value with σ_+ excitation and σ_- excitation, respectively. The blue and red dashed lines are fits for the σ_+ and σ_- excitations, respectively.

maximum to the conduction band minimum. It has been reported that the band-edge excitation can reduce the phonon-assisted intervalley scattering in the conduction band, which in turn enhances the circular dichroism response.^{65,66} A similar result with the excitation of σ_+ incident light is also observed, as shown in Figure 4b. Notably, the σ_- component of the detected PL intensity is always higher than the σ_+ component due to L-MS enhancing the spontaneous emission of the σ_- exciton.

Figure 4c shows that the CD of the interlayer exciton enhances as the excitation wavelength gradually approaches the one corresponding to the bandgap of WS₂ (620 nm) in the

WSe₂/WS₂ heterostructure on the L-MS. With the excitation of 510 nm incidence, the interlayer exciton shows a CD of 13% with σ_- excitation. When the excitation wavelength is increased to 620 nm, the CD jumps significantly to 38% with σ_- excitation. The CD value might be further enhanced by introducing a metasurface based on chiral quasi-bound states in the continuum,⁶⁷ lowering the temperature or introducing the Zeeman-splitting effect by applying a magnetic field.⁵⁷

POTENTIAL OPTICAL COMMUNICATION WITH VALLEY POLARIZATION

Error detection in optical communication systems is crucial for ensuring data integrity, especially in high-speed and quantum communication. It can be achieved through techniques such as one's complement.⁶⁸ This method detects errors caused by bit flips in the data transmission. The sender transmits both the data and its one's complement, which is obtained by flipping each bit of the original data. Upon receiving the data and its complement, the receiver recalculates the one's complement based on the received data and compares it with the received one's complement. If the two are identical, the data are considered without error in transmission. This strategy ensures that both overflows and simple bit errors are more likely to be caught. Considering that the valley polarization of the interlayer exciton PL can be controlled, we design an optical communication approach that allows both direct and byte-invert transmission. Figure 5a shows the experimental setup, where the 532 nm laser passes through a linear polarizer and a quarter-wave plate (QWP). The input message "NJU" is encoded with Morse code.^{69,70} The Morse code represents letters and numbers using sequences of dots (short signals) and dashes (long signals), and the timing of these signals is crucial for the correct interpretation. According to standard Morse timing rules, a dot (·) represents '1', a dash (—) represents '111', an intracharacter gap is a short pause between the dots and dashes within a single character and is represented

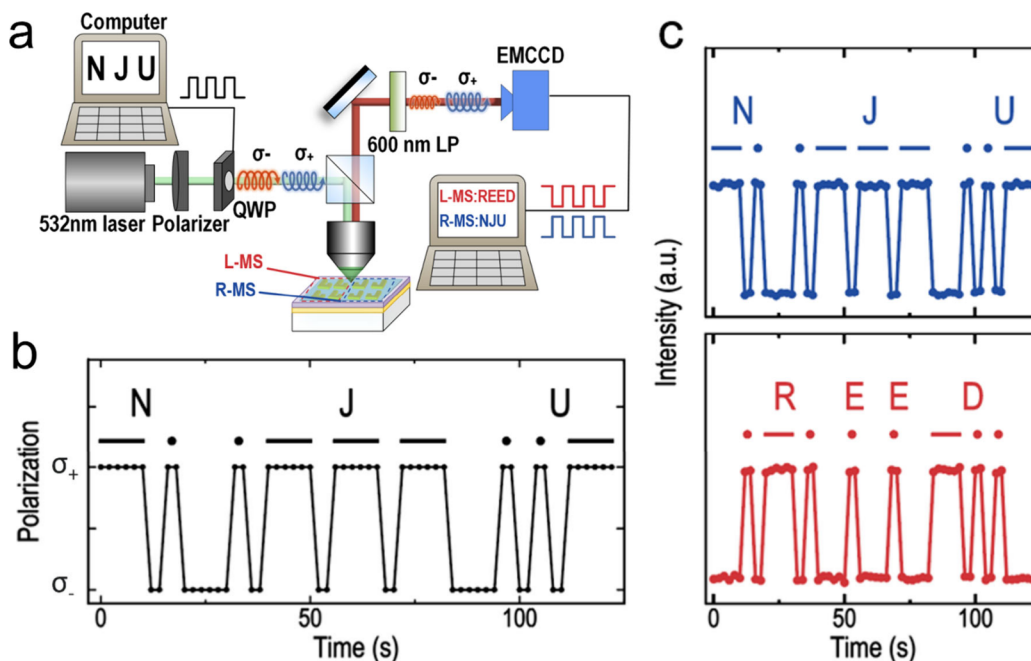


Figure 5. (a) Schematic diagram of the communication system. (b) The input signals. (c) Waveforms of output light signals emitted by the heterostructure on the R-MS (upper panel) and L-MS (lower panel).

by '0', and a short gap between letters is represented by '000'. Using this encoding scheme, each character in 'NJU' is separately encoded as follows: 'N' is encoded as '11101', 'J' is encoded as '1011101110111', 'U' is encoded as '1010111'. When these encoded characters are concatenated with the separator '000' in between, the complete message 'NJU' is encoded as '1110100010111011101110001010111', as shown in Figure 5b. This encoded sequence is then transmitted to the controller, which controls the rotation of QWP. When the controller receives a "1", the fast axis of the QWP will be rotated to -45° with respect to the horizontal direction; when the controller gets a "0", the fast axis of the QWP will be rotated to $+45^\circ$ with respect to the horizontal direction. Therefore, when the controller receives a "1", the emitted light is σ_+ ; when it receives a "0", the emitted light is σ_- .

When the modulated incidence is focused at R-MS, the PL intensity excited by σ_+ is higher. Therefore, the time series of PL intensity collected by the electron-multiplying charge-coupled device (EMCCD) corresponds to '1110100010111011101110001010111', which can be decoded as "NJU", as shown in the upper panel of Figure 5c. However, if the modulated light is focused at L-MS, the PL intensity excited by σ_- is higher. Hence, the PL intensity time series collected by the EMCCD at L-MS is '0001011101000100010001110101000' instead, which is decoded as 'REED', as shown in the lower panel of Figure 5c. In this way, the WSe_2/WS_2 heterostructure-metamaterial acts as a bifunctional device for transmitting optical messages and achieves both direct and byte-invert transmission in optical communication. In principle, we can sum each byte of the direct and byte-inverted transmission outputs, respectively. If every resulting byte equals 1 after this operation, then the data transmission is accurate. Otherwise, errors occurred in transmission. Therefore, the byte-inverted transmission helps to maintain data integrity by reducing the likelihood of errors. This can be particularly useful in optical communication systems, when signal degradation may occur over long distances.

In conclusion, we tuned the valley polarization of the interlayer exciton by covering the WSe_2/WS_2 heterostructure on a dual-handedness metasurface. Physically, each unit cell of the metasurface acts as a chiral nanocavity, and the helicity-dependent strong electric fields induce chiral Purcell effects, which eventually modify the valley-polarized emission of interlayer excitons. With σ_+ excitation, the interlayer exciton CD in WSe_2/WS_2 heterostructures is significantly enhanced on a right-handed metasurface, while on a left-handed metasurface it is sign-inverted with an increased absolute value. Furthermore, the CD of interlayer excitons increases up to 38% as the σ_- excitation wavelength corresponds to the bandgap of WS_2 . Moreover, the WSe_2/WS_2 heterostructure-metamaterial can serve as a bifunctional device for transmitting optical messages and achieving both direct and byte-invert transmission. This functionality enhances data stability and improves error detection, ensuring high integrity in communication systems.

METHODS

Simulation. All simulations are carried out using the finite-difference time-domain (FDTD) method. In the simulation, periodic boundary conditions in the x - and y -directions and perfectly matched layer (PML) boundary conditions in the z -

direction are applied. Plane-wave sources with wavelengths in the range of 700–1000 nm are placed 1 μm from the structure.

Sample Preparation. Au reflection layer (100 nm) and SiO_2 dielectric layer (90 nm) are deposited on the polished Si substrate using a magnetron sputtering system. A layer of photoresist is spin-coated onto the SiO_2 dielectric layer. Then, electron beam lithography (EBL) is employed to define the designed pattern on the sample. After development, a chiral pattern is formed on the photoresist layer. A 30 nm-thick Au layer is then deposited on the sample by electron beam evaporation. Then we apply the chemical lift-off technique by soaking the sample in a resist remover to peel off the photoresist layer. In this way, only the desired Au patterns survive on the SiO_2 layer. Monolayer WSe_2 and WS_2 flakes are mechanically exfoliated and transferred onto the chiral metasurface in a sequential manner to form a heterostructure. Both monolayers are identified by optical microscopy and confirmed by PL and Raman spectra, as shown in Supporting Information in Figure S3.

Optical Measurements. Low-temperature PL measurements are conducted in a temperature-controlled liquid nitrogen bath cryostat (sample in vacuum). PL spectra are acquired on a confocal micro-Raman system (Princeton Instruments, Trenton, NJ) with a 100 $\times$ objective lens. The excitation laser is a 532 nm CW laser focusing on a diffraction-limited spot of about 1 μm . A broadband linear polarizer and a quarter-wave plate (532 nm) are used to initiate circularly polarized light. A pair of broadband linear polarizers and a quarter-wave plate (690–1200 nm) are used as the analyzer placed before the spectrometer.

ASSOCIATED CONTENT

Supporting Information

The Supporting Information is available free of charge at <https://pubs.acs.org/doi/10.1021/acs.nanolett.5c01583>.

Simulated PL spectra, valley-polarized PL spectra, Raman and PL spectra (PDF)

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Author Contributions

[†](Y.Z., K.-L.Z., D.-X.Q.) These authors contributed equally to this work. R.P., Y.Z., and M.W. conceived this work. Y.Z. fabricated the device with the assistance of J.H.; Y.Z., K.L.Z., and D.X.Q. performed the optical experiments; R.P. and M.W. directed and supervised the research. Y.Z., D.X.Q., R.P., and M.W. wrote the manuscript.

Notes

The authors declare no competing financial interest.

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